

**AMENDMENTS TO THE SPECIFICATION:**

Amend the paragraph in lines 3-23 on page 2 to read:

In addition, in the technique of packaging (sealing) a semiconductor element in the field of semiconductor devices in the recent years, one-sided sealing-type semiconductor devices, for instance, have been remarked and actually used. A semiconductor device in which a semiconductor element is sealed by a cured product of an epoxy resin composition has excellent mass-productibility and low costs. Further, the above-mentioned one-sided sealing type semiconductor device can have high performance by highly integrating the semiconductor element. In addition, in a method of mounting a semiconductor element to a board, which is the insulating substrate mentioned above in a flip chip manner or a direct chip attachment manner, sealing is usually carried out by one-sided sealing in a state of incorporating the semiconductor element, or alternatively by filling a molten thermosetting resin composition in a void between the insulating substrate and the semiconductor device and curing the composition. However, these semiconductor devices have some problems of generation of bowing of the package caused by curing shrinkage of a sealing resin, and incongruence in the coefficients of linear expansion of the insulating substrate and the sealing resin (cured product). In the semiconductor device in which the bowing described above is generated, ~~peeling~~ peeling or the like is caused at the sealing interface by the stress due to bowing, so that its reliability

is lowered, thereby resulting in poor applicability to a substrate. Therefore, a solution to such a problem is desired.

Amend the paragraph bridging pages 11-12 to read:

Further, as a flame retarder other than the flame retarders mentioned above, there can be used composite metal hydroxide having a polyhedral shape represented by the general formula (2):



wherein M is at least one metal atom selected from the group consisting of Mg, Ca, Sn and Ti; Q is at least one metal atom selected from the group consisting of Mn, Fe, Co, Ni, Cu and Zn; and X is a positive number of 0.01 to 0.5. This composite metal hydroxide has the crystalline structure of a polyhedral form. It does not have a conventional hexahedral form, or a ~~platy~~ plate-like form having thin thickness such as scaly form for the crystalline structure. Rather, it refers to a composite metal hydroxide having large crystal growth in the direction of thickness (c-axis direction) as well as in the length and width directions, including, for instance, those having a granular crystalline form which are made to resemble steric and spherical form by the crystal growth of ~~platy~~ plate-like crystal in the direction of thickness (c-axis direction), the granular crystalline forms including, approximate dodecahedron, approximate octahedron, approximate tetrahedron, and the like.